The RF Line

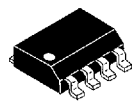
NPN Silicon RF Low Power Transistor

Designed for amplifier, frequency multiplier, or oscillator applications in industrial equipment constructed with surface mount components. Suitable for use as output driver or pre–driver stages in VHF and UHF equipment.

- Low Cost SORF Plastic Surface Mount Package
- Guaranteed RF Specification — $|S_{21}|^2$
- S–Parameter Characterization
- Low Voltage Version of MRF3866
- Tape and Reel Packaging Options Available by adding R2 suffix. R2 suffix = 2,500 units per reel

MRF4427, R2

1.0 W, 175 MHz
HIGH–FREQUENCY
TRANSISTOR
NPN SILICON



CASE 751–05, STYLE 1
SORF
(SO–8)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	20	Vdc
Collector–Base Voltage	V_{CBO}	40	Vdc
Emitter–Base Voltage	V_{EBO}	2.0	Vdc
Collector Current — Continuous	I_C	400	mAdc
Total Device Dissipation @ T_C = 75°C Derate above 75°C	P_D	1.67 22.2	Watts mW/°C
Operating Junction and Storage Temperature Range	T_J, T_{stg}	–65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	45	°C/W

DEVICE MARKING

MRF4427 = 4427

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

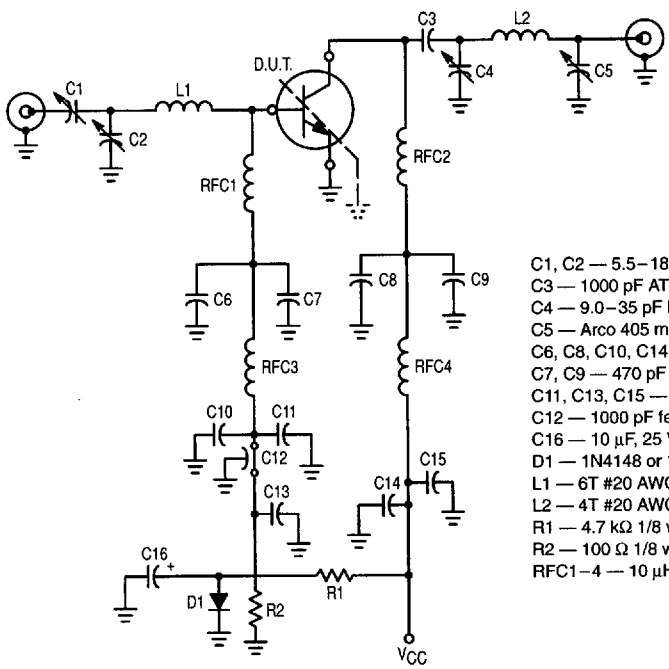
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (I_C = 5.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	20	—	—	Vdc
Collector–Emitter Breakdown Voltage (I_C = 5.0 mAdc, R_{BE} = 10 ohms)	$V_{(BR)CER}$	40	—	—	Vdc
Emitter–Base Breakdown Voltage (I_E = 100 μAdc)	$V_{(BR)EBO}$	2.0	—	—	Vdc
Collector Cutoff Current (V_{CE} = 12 Vdc, I_B = 0)	I_{CEO}	—	—	20	μAdc

NOTE:
1. Case temperature measured on collector lead immediately adjacent to body of package.

(continued)

ELECTRICAL CHARACTERISTICS — continued (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
DC Current Gain (I_C = 100 mAdc, V_{CE} = 5.0 Vdc) (I_C = 360 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}	 10 5.0	 50 —	 200 —	—
Collector–Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 20 mAdc)	$V_{CE(sat)}$	—	60	—	mVdc
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (I_C = 50 mAdc, V_{CE} = 12 Vdc, f = 200 MHz)	f_T	—	1600	—	MHz
Output Capacitance (V_{CB} = 12 Vdc, I_E = 0, f = 1.0 MHz)	C_{ob}	—	—	3.0	pF
FUNCTIONAL TESTS					
Common–Emitter Amplifier Power Gain (P_{in} = 15 mW, V_{CC} = 12 Vdc, f = 175 MHz)	G_{pe}	—	18	—	dB
Collector Efficiency (Figure 1) (P_{out} = 1.0 W, V_{CC} = 12 Vdc, f = 175 MHz)	η	—	60	—	%
Insertion Gain (V_{CE} = 12 Vdc, I_C = 50 mA, f = 200 MHz)	$\|S_{21}\|^2$	14	16.4	—	dB



C1, C2 — 5.5–18 pF Erie ceramic trimmer
C3 — 1000 pF ATC 100 mil chip cap.
C4 — 9.0–35 pF Erie ceramic trimmer
C5 — Arco 405 mica trimmer
C6, C8, C10, C14 — 0.1 μF Erie blue cap.
C7, C9 — 470 pF ATC 100 mil chip cap.
C11, C13, C15 — 1.0 μF Erie blue cap, non–polar
C12 — 1000 pF feedthru
C16 — 10 μF, 25 V tantalum
D1 — 1N4148 or 1N914
L1 — 6T #20 AWG on #2 drill bit
L2 — 4T #20 AWG on #4 drill bit
R1 — 4.7 kΩ 1/8 watt carbon
R2 — 100 Ω 1/8 watt carbon
RFC1–4 — 10 μH molded choke

Figure 1. 175 MHz RF Amplifier Circuit for Functional Tests

TYPICAL CHARACTERISTICS

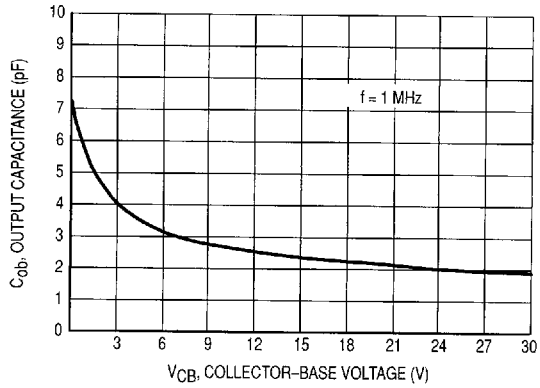


Figure 2. Collector–Base Capacitance versus Voltage

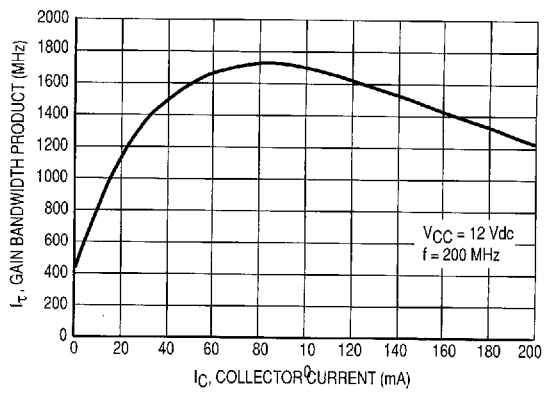


Figure 3. Gain Bandwidth Product versus Collector Current

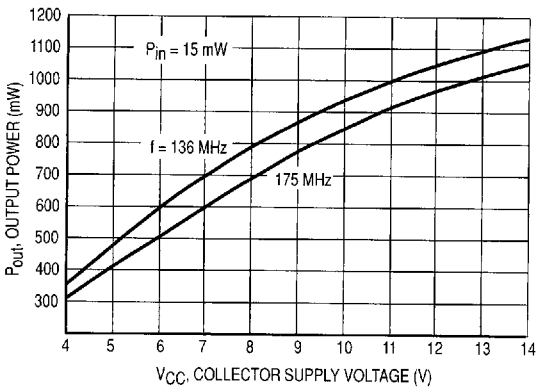


Figure 4. Output Power versus Voltage

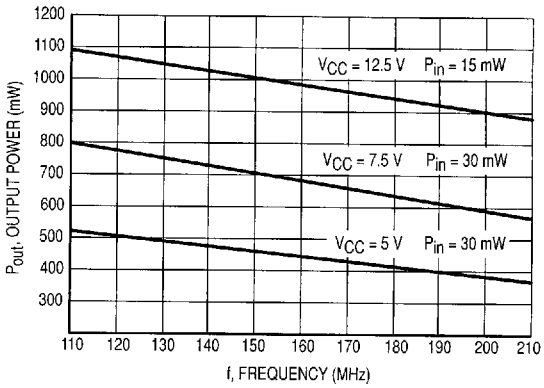


Figure 5. Output Power versus Frequency

V_{CE} (Volts)	I_C (mA)	f (MHz)	S_{11}		S_{21}		S_{12}		S_{22}	
			$\|S_{11}\|$	$\angle\phi$	$\|S_{21}\|$	$\angle\phi$	$\|S_{12}\|$	$\angle\phi$	$\|S_{22}\|$	$\angle\phi$
5.0	5.0	50	0.82	−104	10.3	125	0.05	38	0.68	−34
		100	0.83	−141	6.1	103	0.06	26	0.51	−40
		200	0.81	−165	3.2	85	0.07	21	0.44	−46
		500	0.80	169	1.3	57	0.07	32	0.49	−73
		750	0.79	156	0.8	42	0.08	49	0.58	−94
		1000	0.76	144	0.6	30	0.11	61	0.65	−114
	25	50	0.77	−151	19	107	0.02	36	0.35	−75
		100	0.79	−168	9.9	94	0.03	37	0.21	−87
		200	0.79	−180	5.0	82	0.04	49	0.16	−97
		500	0.78	163	2.0	61	0.07	62	0.22	−106
		750	0.77	152	1.3	48	0.10	66	0.31	−115
		1000	0.74	141	0.9	36	0.13	66	0.37	−127
	50	50	0.77	−163	21.1	103	0.02	37	0.29	−98
		100	0.79	−174	10.7	92	0.02	50	0.19	−119
		200	0.79	177	5.4	82	0.03	62	0.16	−134
		500	0.78	162	2.2	62	0.07	67	0.20	−131
		750	0.77	151	1.4	50	0.10	69	0.26	−130
		1000	0.74	140	1.1	38	0.13	67	0.32	−139
12	5.0	50	0.83	−97	11	129	0.04	46	0.75	−26
		100	0.82	−135	6.8	107	0.05	29	0.61	−29
		200	0.81	−162	3.6	88	0.05	24	0.54	−34
		500	0.79	171	1.4	60	0.06	37	0.47	−57
		750	0.78	157	0.9	44	0.07	55	0.64	−76
		1000	0.75	145	0.7	32	0.09	68	0.70	−95
	25	50	0.73	−143	22.1	111	0.02	38	0.43	−52
		100	0.76	−164	11.7	96	0.02	39	0.29	−52
		200	0.77	−177	6.0	84	0.03	48	0.22	−53
		500	0.76	165	2.4	63	0.06	64	0.27	−69
		750	0.75	154	1.6	49	0.08	67	0.35	−84
		1000	0.72	143	1.1	38	0.11	69	0.42	−98
	50	50	0.73	−156	25.5	106	0.02	41	0.32	−67
		100	0.75	−171	13.1	94	0.02	49	0.20	−69
		200	0.76	59	6.6	83	0.03	60	0.15	−71
		500	0.75	164	2.6	64	0.06	69	0.20	−81
		750	0.74	153	1.7	51	0.09	70	0.27	−92
		1000	0.71	142	1.2	38	0.12	70	0.34	−104

Table 1. Common Emitter S–Parameters

Freq. (MHz)	P_{in} (mW)	P_{out} (mW)	V_{CC} (Volts)	Z_{in} (Ohms)	Z_{OL}^* (Ohms)
136	15	—	12.5	6.2 – j11.6	—
175	15	—	12.5	4.6 – j10.4	—
136	—	1000	12.5	—	47.7 + j41.7
175	—	1000	12.5	—	47.4 – j34.4
136	30	—	7.5	5.65 – j12.6	—
175	30	—	7.5	6.25 – j12.2	—
136	—	650	7.5	—	27.6 – j32.4
175	—	650	7.5	—	27.9 – j27.6
136	30	—	5.0	6.1 – j13.3	—
175	30	—	5.0	5.9 – j12.22	—
136	—	450	5.0	—	24.8 – j22.8
175	—	450	5.0	—	28.3 – j29.3

Z_{OL}^* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

Table 2. Series Input/Output Impedances